



August 2014

FCP20N60 / FCPF20N60

N-Channel SuperFET[®] MOSFET

600 V, 20 A, 190 mΩ

Features

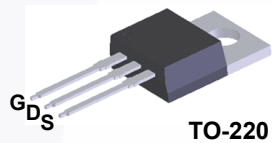
- 650V @ $T_J = 150^{\circ}\text{C}$
- Typ. $R_{DS(on)} = 150\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 75\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 165\text{ pF}$)
- 100% Avalanche Tested

Applications

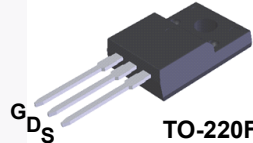
- Solar Inverter
- AC-DC Power Supply

Description

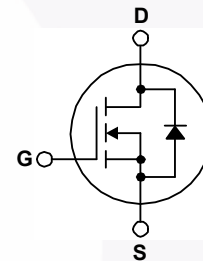
SuperFET[®] MOSFET is Fairchild Semiconductor's first generation of high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



TO-220



TO-220F



Absolute Maximum Ratings

Symbol	Parameter	FCP20N60	FCPF20N60	Unit
V_{DSS}	Drain-Source Voltage	600		V
I_D	Drain Current - Continuous ($T_C = 25^{\circ}\text{C}$) - Continuous ($T_C = 100^{\circ}\text{C}$)	20	20*	A
		12.5	12.5*	A
I_{DM}	Drain Current - Pulsed (Note 1)	60	60*	A
V_{GSS}	Gate-Source Voltage	± 30		V
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	690		mJ
I_{AR}	Avalanche Current (Note 1)	20		A
E_{AR}	Repetitive Avalanche Energy (Note 1)	20.8		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
P_D	Power Dissipation ($T_C = 25^{\circ}\text{C}$) - Derate Above 25°C	208	39	W
		1.67	0.3	W/ $^{\circ}\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150		$^{\circ}\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300		$^{\circ}\text{C}$

*Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FCP20N60	FCPF20N60	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	0.6	3.2	$^{\circ}\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^{\circ}\text{C/W}$

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCP20N60	FCP20N60	TO-220	Tube	N/A	N/A	50 units
FCPF20N60	FCPF20N60	TO-220F	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
--------	-----------	-----------------	------	------	------	------

Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$, $T_J = 25^\circ\text{C}$	600	-	-	V
		$I_D = 250\ \mu\text{A}$, $V_{GS} = 0\ \text{V}$, $T_J = 150^\circ\text{C}$	-	650	-	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$, Referenced to 25°C	-	0.6	-	V/ $^\circ\text{C}$
BV_{DS}	Drain-Source Avalanche Breakdown Voltage	$V_{GS} = 0\ \text{V}$, $I_D = 20\ \text{A}$	-	700	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	-	1	μA
		$V_{DS} = 480\ \text{V}$, $T_C = 125^\circ\text{C}$	-	-	10	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 30\ \text{V}$, $V_{DS} = 0\ \text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\ \mu\text{A}$	3.0	-	5.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\ \text{V}$, $I_D = 10\ \text{A}$	-	0.15	0.19	Ω
g_{FS}	Forward Transconductance	$V_{DS} = 40\ \text{V}$, $I_D = 10\ \text{A}$	-	17	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	-	2370	3080	pF
C_{oss}	Output Capacitance		-	1280	1665	pF
C_{rss}	Reverse Transfer Capacitance		-	95	-	pF
C_{oss}	Output Capacitance	$V_{DS} = 480\ \text{V}$, $V_{GS} = 0\ \text{V}$, $f = 1\ \text{MHz}$	-	65	85	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\ \text{V}$ to $400\ \text{V}$, $V_{GS} = 0\ \text{V}$	-	165	-	pF
Q_g	Total Gate Charge at 10V	$V_{DS} = 480\ \text{V}$, $I_D = 20\ \text{A}$, $V_{GS} = 10\ \text{V}$ (Note 4)	-	75	98	nC
Q_{gs}	Gate to Source Gate Charge		-	13.5	18	nC
Q_{gd}	Gate to Drain "Miller" Charge		-	36	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 300\ \text{V}$, $I_D = 20\ \text{A}$, $V_{GS} = 10\ \text{V}$, $R_G = 25\ \Omega$ (Note 4)	-	62	135	ns
t_r	Turn-On Rise Time		-	140	290	ns
$t_{d(off)}$	Turn-Off Delay Time		-	230	470	ns
t_f	Turn-Off Fall Time		-	65	140	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	20	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	60	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0 V, I _{SD} = 20 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _{SD} = 20 A, dI _F /dt = 100 A/μs	-	530	-	ns
Q _{rr}	Reverse Recovery Charge		-	10.5	-	μC

Notes:

- 1: Repetitive rating; pulse-width limited by maximum junction temperature.
- 2: $I_{AS} = 10\ \text{A}$, $V_{DD} = 50\ \text{V}$, $R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
- 3: $I_{SD} \leq 20\ \text{A}$, $di/dt \leq 200\ \text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, starting $T_J = 25^\circ\text{C}$.
- 4: Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

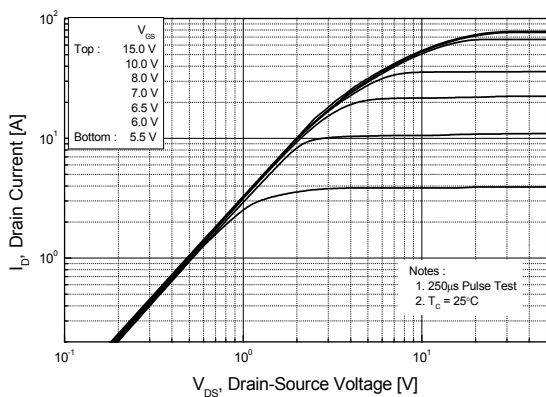


Figure 2. Transfer Characteristics

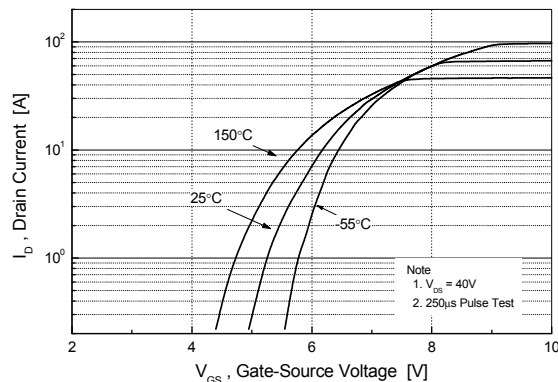


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

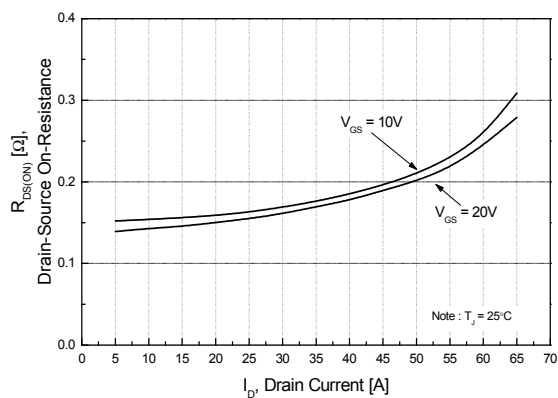


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

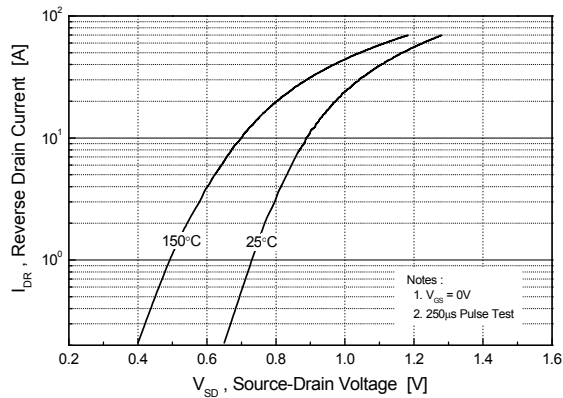


Figure 5. Capacitance Characteristics

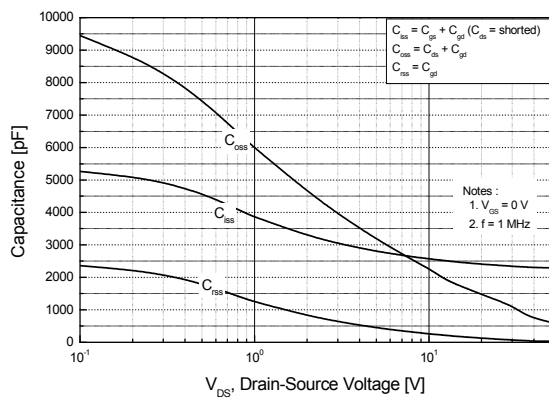
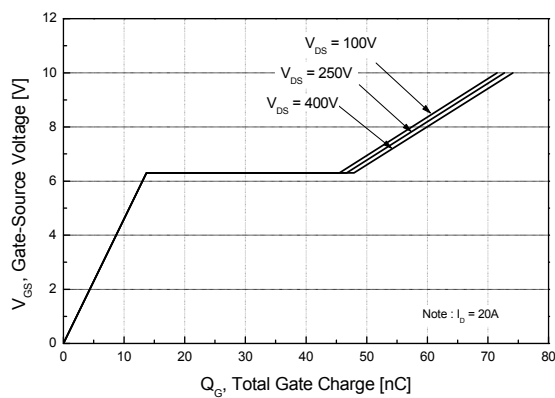


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

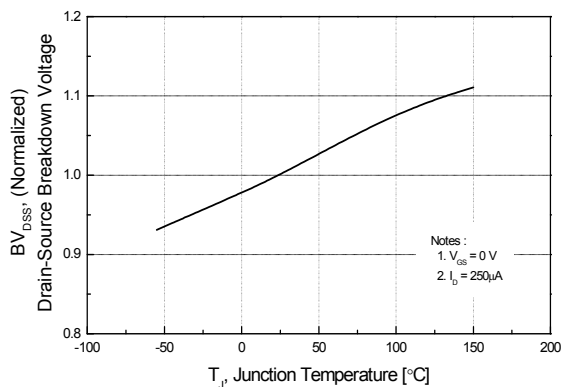


Figure 8. On-Resistance Variation vs. Temperature

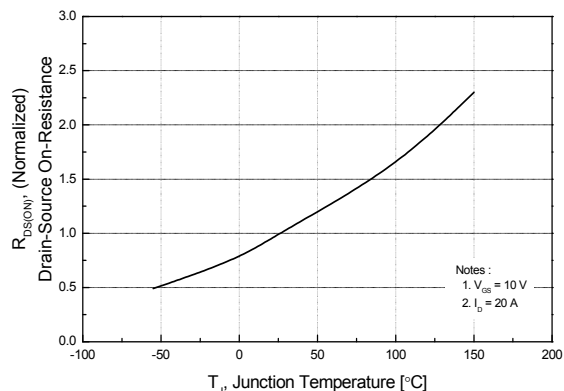


Figure 9-1. Maximum Safe Operating Area for FCP20N60

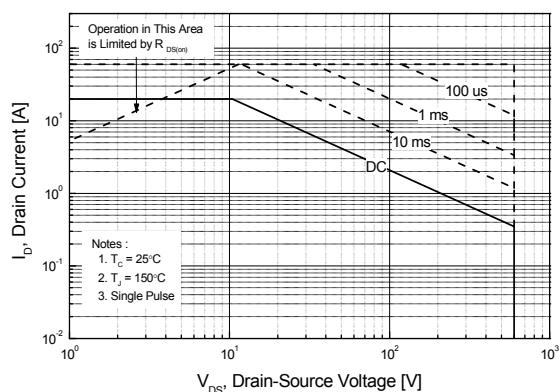


Figure 9-2. Maximum Safe Operating Area for FCPF20N60

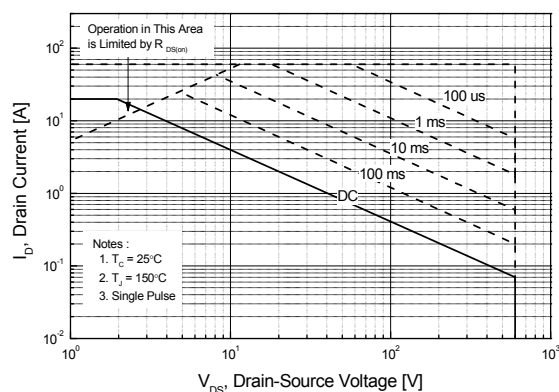
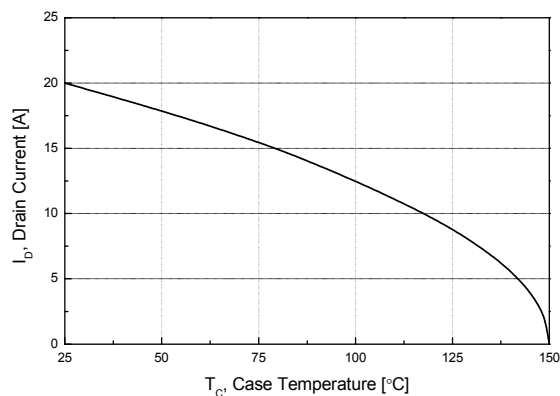


Figure 10. Maximum Drain Current vs. Case Temperature



Typical Performance Characteristics (Continued)

Figure 11-1. Transient Thermal Response Curve for FCP20N60

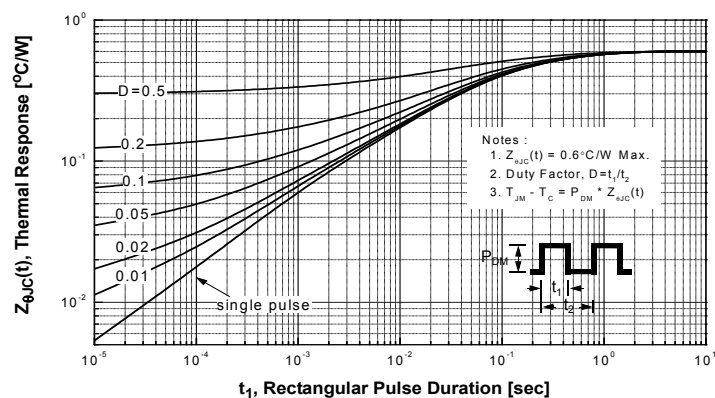


Figure 11-2. Transient Thermal Response Curve for FCPF20N60

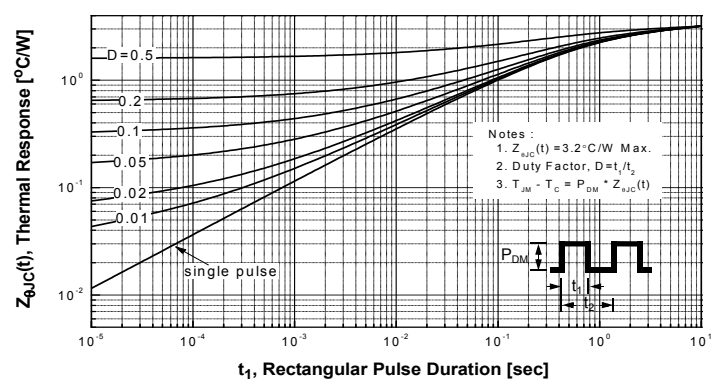




Figure 12. Gate Charge Test Circuit & Waveform

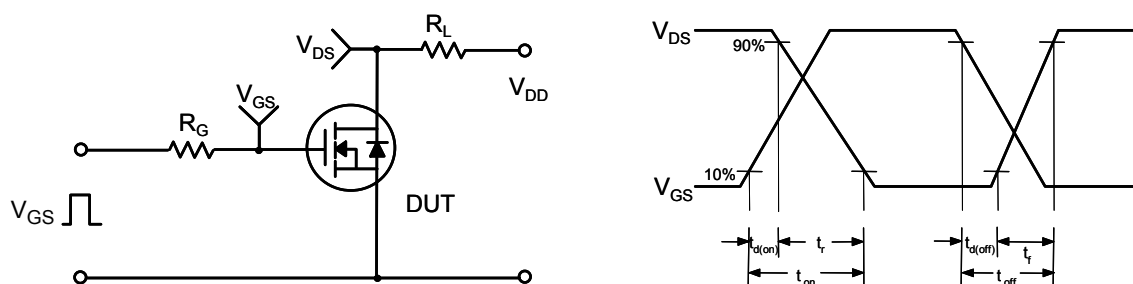


Figure 13. Resistive Switching Test Circuit & Waveforms

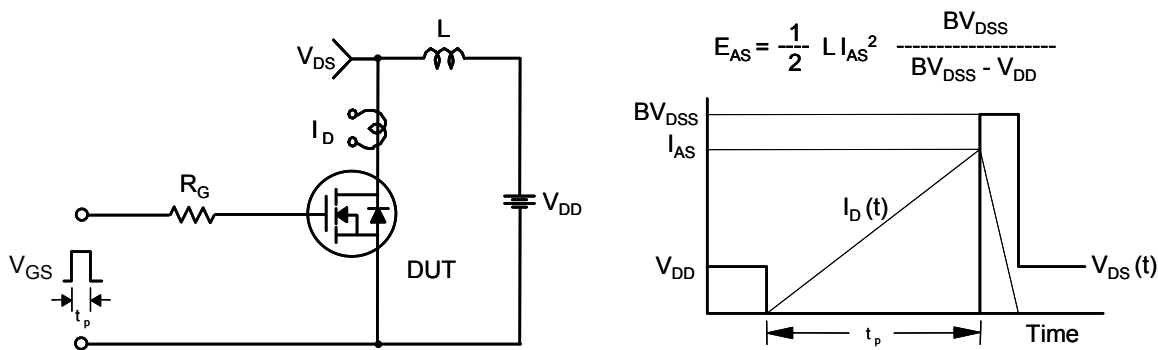
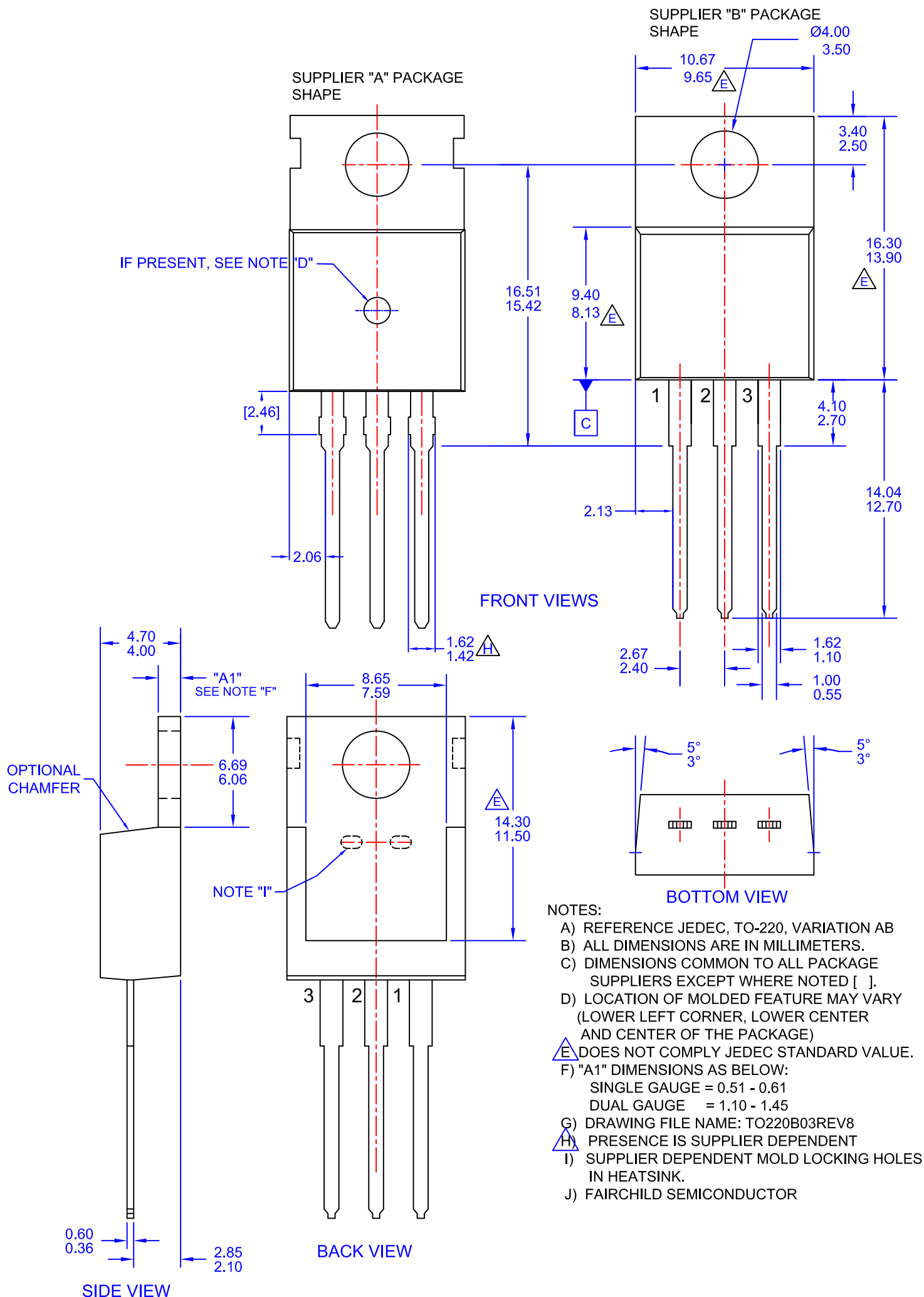
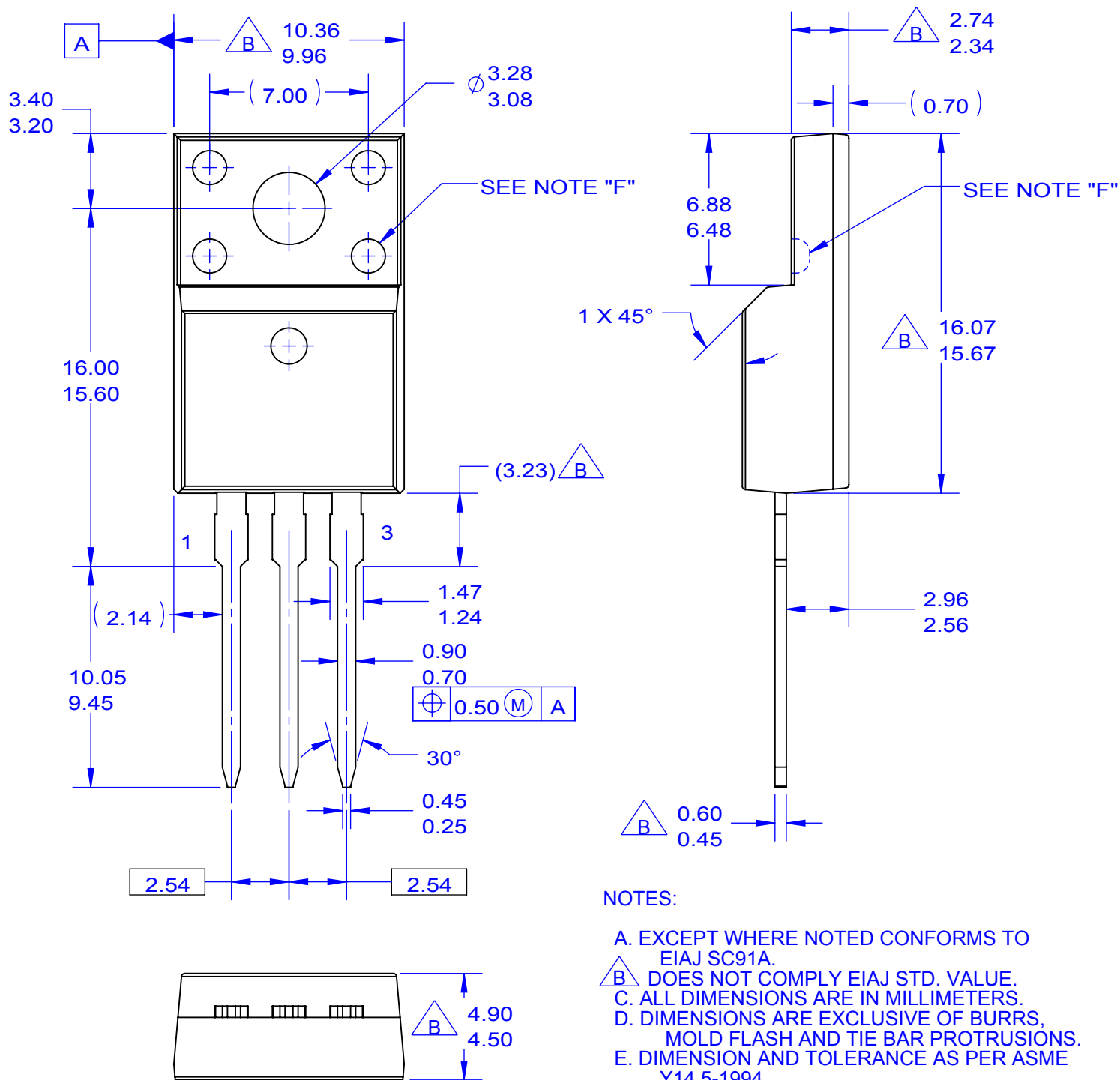


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





NOTES:

- A. EXCEPT WHERE NOTED CONFORMS TO EIAJ SC91A.
- B. DOES NOT COMPLY EIAJ STD. VALUE.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.
- E. DIMENSION AND TOLERANCE AS PER ASME Y14.5-1994.
- F. OPTION 1 - WITH SUPPORT PIN HOLE.
OPTION 2 - NO SUPPORT PIN HOLE.
- G. DRAWING FILE NAME: TO220M03REV3



TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

AccuPower™	F-PFS™	OPTOPLANAR®	SYSTEM GENERAL®*
AttitudeEngine™	FRFET®	 ®	TinyBoost®
Awinda®	Global Power Resource™	PowerTrench®	TinyBuck®
AX-CAP®*	GreenBridge™	PowerXS™	TinyCalc™
BitSiC™	Green FPS™	Programmable Active Droop™	TinyLogic®
Build it Now™	Green FPS™ e-Series™	QFET®	TINYOPTO™
CorePLUS™	Gmax™	QS™	TinyPower™
CorePOWER™	GTO™	Quiet Series™	TinyPWM™
CROSSVOLT™	IntelliMAX™	RapidConfigure™	TinyWire™
CTL™	ISOPLANAR™	 ™	TranSiC™
Current Transfer Logic™	Making Small Speakers Sound Louder and Better™	Saving our world, 1mW/W/kW at a time™	TriFault Detect™
DEUXPEED®	MegaBuck™	SignalWise™	TRUECURRENT®*
Dual Cool™	MICROCOUPLER™	SmartMax™	μSerDes™
EcoSPARK®	MicroFET™	SMART START™	 SerDes®
EfficientMax™	MicroPak™	Solutions for Your Success™	UHC®
ESBC™	MicroPak2™	SPM®	Ultra FRFET™
 ®	MillerDrive™	STEALTH™	UniFET™
Fairchild®	MotionMax™	SuperFET®	VCX™
Fairchild Semiconductor®	MotionGrid®	SuperSOT™-3	VisualMax™
FACT Quiet Series™	MTi®	SuperSOT™-6	VoltagePlus™
FACT®	MTx®	SuperSOT™-8	XS™
FAST®	MVN®	SupreMOS®	Xsens™
FastvCore™	mWSaver®	SyncFET™	仙童™
FETBench™	OptoHit™	Sync-Lock™	
FPS™	OPTOLOGIC®		

* Trademarks of System General Corporation, used under license by Fairchild Semiconductor.

DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. TO OBTAIN THE LATEST, MOST UP-TO-DATE DATASHEET AND PRODUCT INFORMATION, VISIT OUR WEBSITE AT [HTTP://WWW.FAIRCHILDSEMI.COM](http://www.fairchildsemi.com). FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

ANTI-COUNTERFEITING POLICY

Fairchild Semiconductor Corporation's Anti-Counterfeiting Policy. Fairchild's Anti-Counterfeiting Policy is also stated on our external website, www.fairchildsemi.com, under Sales Support.

Counterfeiting of semiconductor parts is a growing problem in the industry. All manufacturers of semiconductor products are experiencing counterfeiting of their parts. Customers who inadvertently purchase counterfeit parts experience many problems such as loss of brand reputation, substandard performance, failed applications, and increased cost of production and manufacturing delays. Fairchild is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. Fairchild strongly encourages customers to purchase Fairchild parts either directly from Fairchild or from Authorized Fairchild Distributors who are listed by country on our web page cited above. Products customers buy either from Fairchild directly or from Authorized Fairchild Distributors are genuine parts, have full traceability, meet Fairchild's quality standards for handling and storage and provide access to Fairchild's full range of up-to-date technical and product information. Fairchild and our Authorized Distributors will stand behind all warranties and will appropriately address any warranty issues that may arise. Fairchild will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. Fairchild is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.

PRODUCT STATUS DEFINITIONS

Definition of Terms

Datasheet Identification	Product Status	Definition
Advance Information	Formative / In Design	Datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	Datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve the design.
Obsolete	Not In Production	Datasheet contains specifications on a product that is discontinued by Fairchild Semiconductor. The datasheet is for reference information only.

Rev. I73